TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N-CHANNEL IGBT

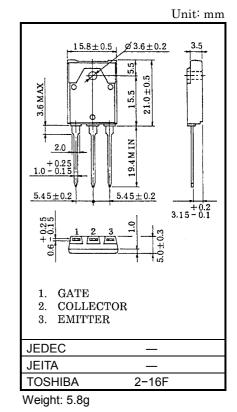
GT40M101

HIGH POWER SWITCHING APPLICATIONS

- High Input Impedance
- High Speed
- : $t_f = 0.4 \mu s$ (Max.)
- Low Saturation Voltage : VCE(sat) = 3.4V (Max.)
- Enhancement-Mode

MAXIMUM RATINGS (Ta = 25°C)

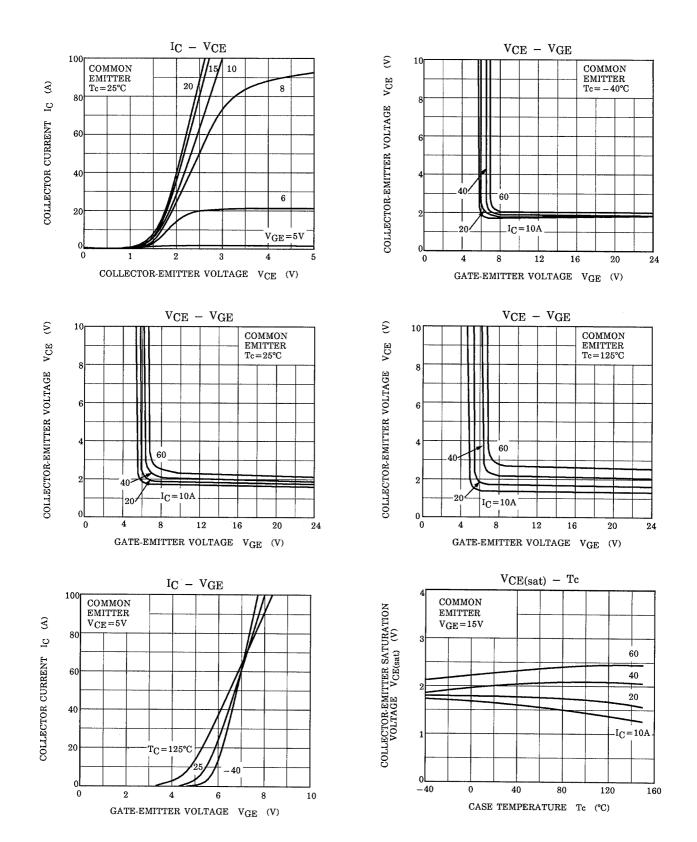
CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	900	V	
Gate-Emitter Voltage		V _{GES}	±25	V	
Collector Current	DC	Ι _C	40	A	
	1ms	I _{CP}	80		
Collector Power Dissipation (Tc = 25°C)		P _C	90	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	-55~150	°C	
Screw Torque		_	0.8	N∙m	



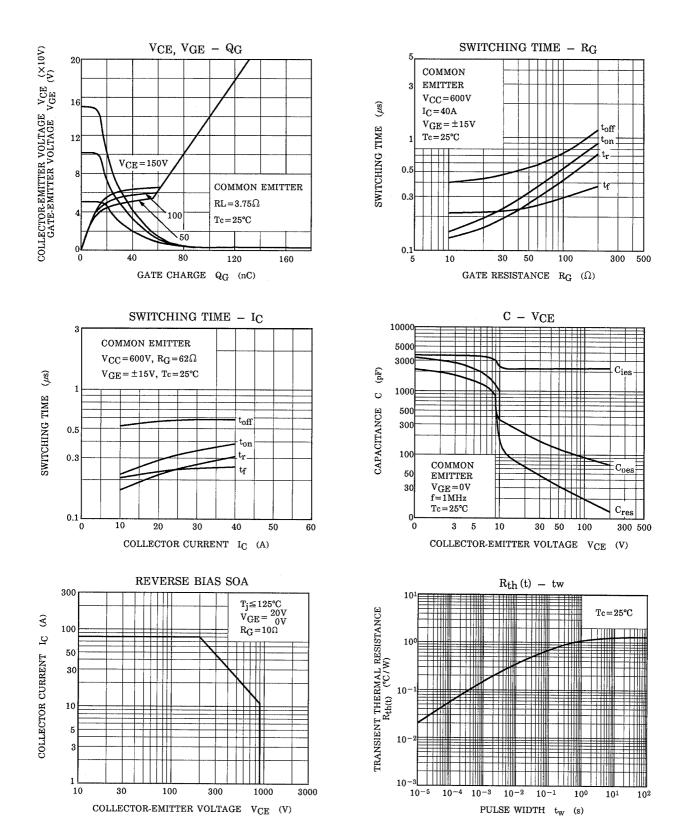
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

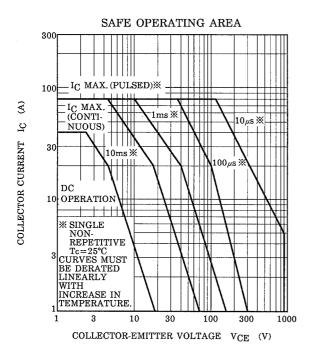
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I _{GES}	V_{GE} = ±25V, V_{CE} = 0	_	_	±500	nA
Collector Cut-off Cu	urrent	ICES	V _{CE} = 900V, V _{GE} = 0	_	_	1.0	mA
Gate-Emitter Cut-c	off Voltage	V _{GE(OFF)}	I _C = 40mA, V _{CE} = 5V	3.0	_	6.0	V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C = 40A, V _{GE} = 15V	_	2.1	3.4	V
Input Capacitance		C _{ies}	V _{CE} = 30V, V _{GE} = 0, f = 1MHz	_	2100	_	pF
Switching Time	Rise Time	t _r	$ \begin{array}{c} \begin{array}{c} & & & & & \\ 15V \\ 0 \end{array} \\ \end{array} \\ \begin{array}{c} & & & \\ 0 \end{array} \\ -15V \end{array} \\ \begin{array}{c} & & & \\ & & \\ & & \\ \end{array} \\ V_{CC} = 600V \end{array} \end{array} $	_	0.30	_	μs
	Turn-On Time	t _{on}		_	0.40	_	
	Fall Time	t _f		_	0.25	0.40	
	Turn-Off Time	t _{off}		_	0.60	_	
Thermal Resistance		R _{th(j-c)}	—	_	—	1.39	°C/W

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